

What does precision mean for an op amp?

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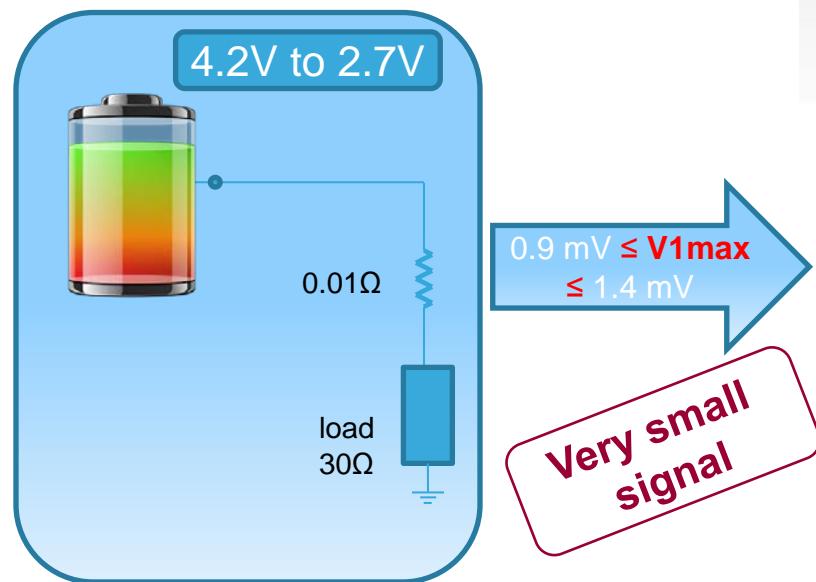
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Why op amps and why precision

Battery fuel gauging



STM32 power supply:
1.65V to 3.6V

ADC
12bits

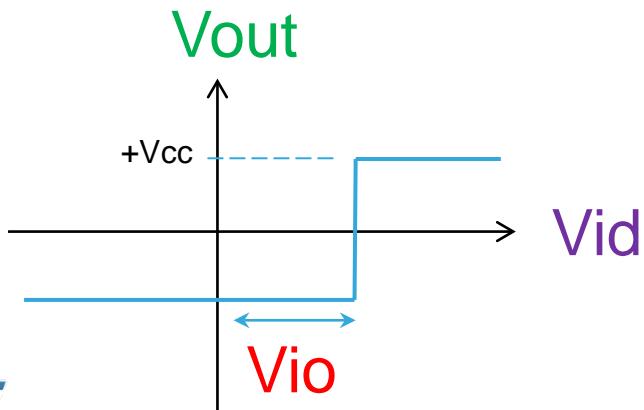
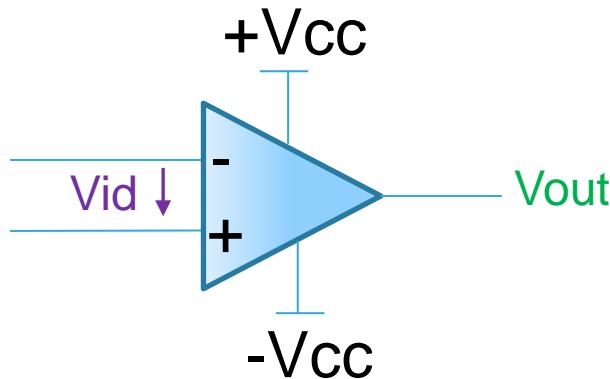


LSB of the ADC
 $= 3.6V / 2^{12}$
 $= 0.88 \text{ mV} !$



Input offset voltage What is this?

- V_{io} offset



<u>LM324</u>					
Symbol	Parameter	Min.	Typ.	Max.	Unit
V_{io}	Input offset voltage ⁽¹⁾ $T_{amb} = +25^\circ C$ LM124-LM224 LM324		2	5	mV
	$T_{min} \leq T_{amb} \leq T_{max}$ LM124-LM224 LM324		7	9	
V_{io}	$V_{icm} = 0$ to $3.8 V$, $T=25^\circ C$ TS507C full temperature range TS507I full temperature range	25	100	250	μV
	$V_{icm} = 0 V$ to $5 V$, $T=25^\circ C$ TS507C full temperature range TS507I full temperature range	400	450	550	

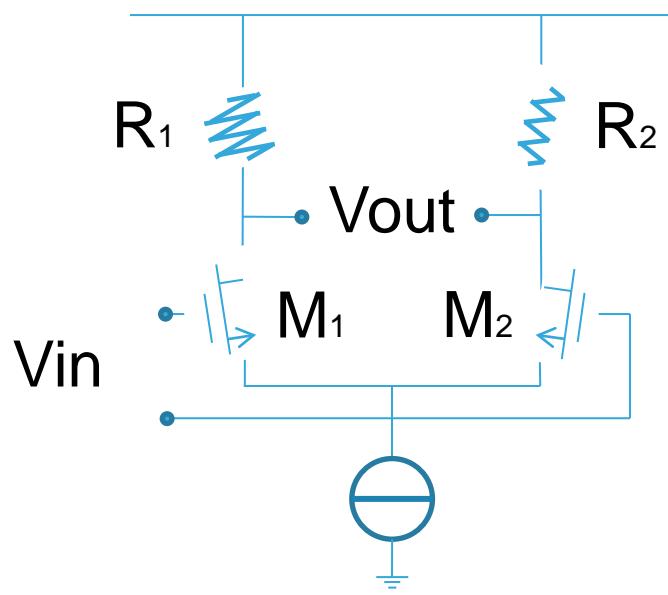
<u>TS507</u>					
V_{io}	Input offset voltage ⁽²⁾	$V_{icm} = 0$ to $3.8 V$, $T=25^\circ C$ TS507C full temperature range TS507I full temperature range	25	100	μV
		$V_{icm} = 0 V$ to $5 V$, $T=25^\circ C$ TS507C full temperature range TS507I full temperature range	400	450	

<u>TSZ121</u> (Very high accuracy)					
Symbol	Parameter	Conditions	Min.	Typ.	Max.
DC performance					
V_{io}	Input offset voltage	$T = 25^\circ C$	1	5	μV
		$-40^\circ C < T < 125^\circ C$		8	
$\Delta V_{io}/\Delta T$	Input offset voltage drift ⁽¹⁾	$-40^\circ C < T < 125^\circ C$	10	30	nV/C



Input offset voltage Where does it comes from?

- Differential input



Component mismatch
 $R_1 \neq R_2, M_1 \neq M_2 \Rightarrow \text{offset}$

For CMOS technology

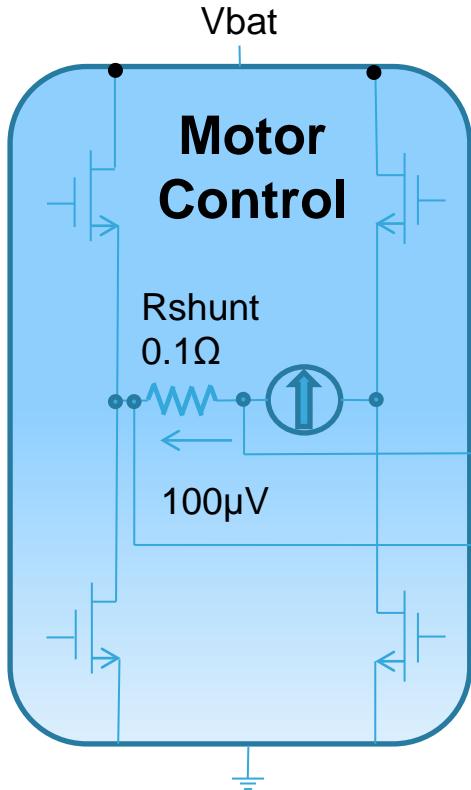
$$V_{os} = \Delta V_{th} + \frac{V_{GS} - VT}{2} \left(\frac{\Delta R}{R} + \frac{\Delta k'}{k'} + \frac{\Delta W/L}{W/L} \right)$$

ΔV_{th} linked to the substrate doping
Second term linked to the size of MOS

Mismatch is mainly due to:

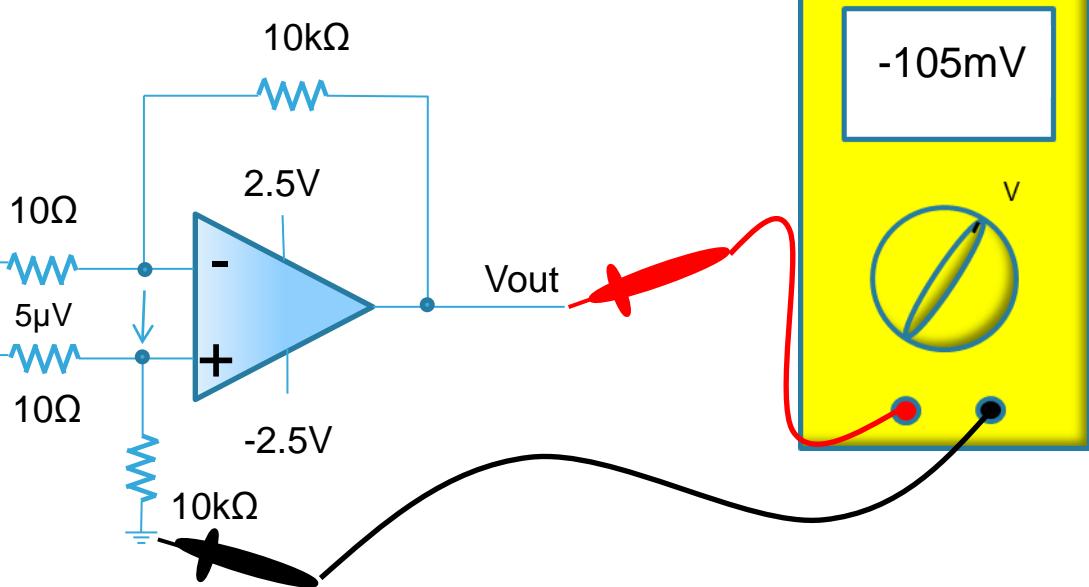
- Doping variations
- Lithographic errors
- Packaging & local stress

Impact of V_{IO} on a real application current sensing for Motor control



$I=1\text{mA}$

$$V_{out} = R_{shunt} \cdot I \cdot \left(\frac{10\text{k}\Omega}{10\Omega} - V_{IO} \left(1 + \frac{10\text{k}\Omega}{10\Omega} \right) \right)$$



TSZ121
 $V_{IO}=5\mu\text{V}$

5% error on speed information
rotation information is correct



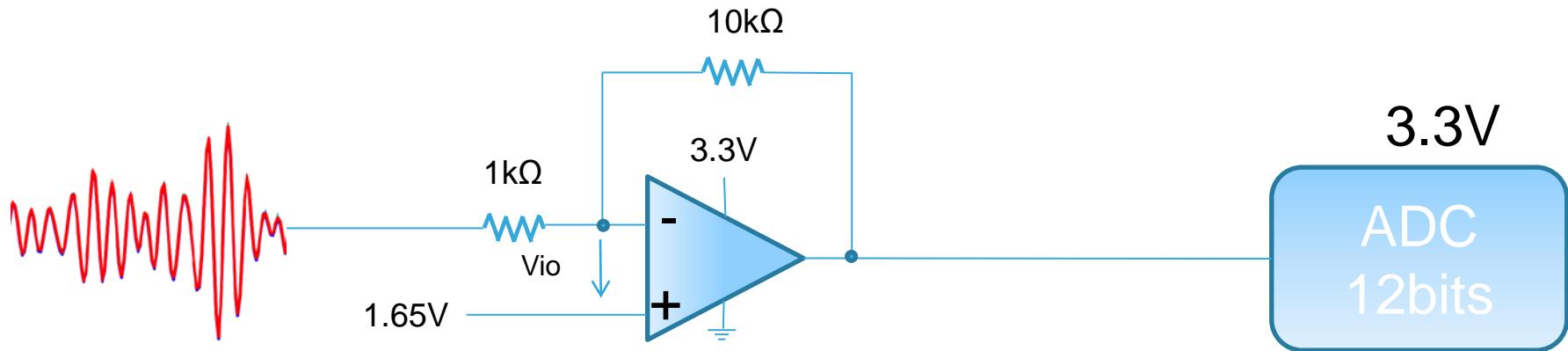
Summary of V_{IO} impact on motor control applications

Opamp	Offset @ 25°C	V_{OUT} for a current $I = 1 \text{ mA}$	Comment
Ideal	0 μV	100 mV	Theoretical measurement in a perfect world!
<u>TS507</u>	+100 μV	-100 μV	Speed of the motor is incorrect. Information about the motor rotation is incorrect
	-100 μV	200 mV	100% error on motor speed Information about the motor rotation is correct
<u>TSZ121</u>	+5 μV	95 mV	5% error on the motor speed Information about the motor rotation is correct
	-5 μV	-105 mV	5% error on the motor speed Information about motor rotation is correct



The real cost of V_{IO} !

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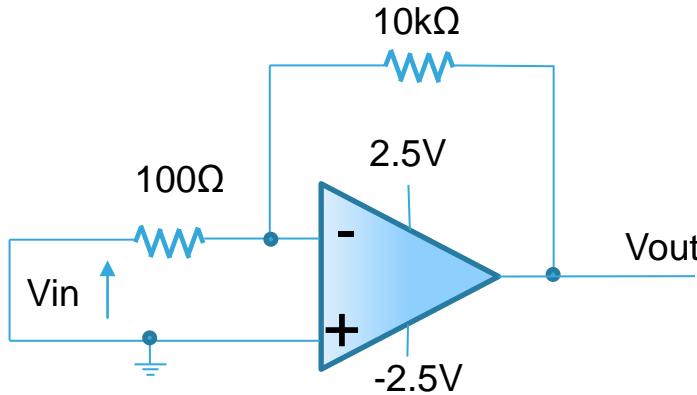


The LSB of the ADC is $3.3 \text{ V}/2^{12} = 805 \text{ }\mu\text{V}$

The input signal is amplified by -10, and the V_{IO} by 11

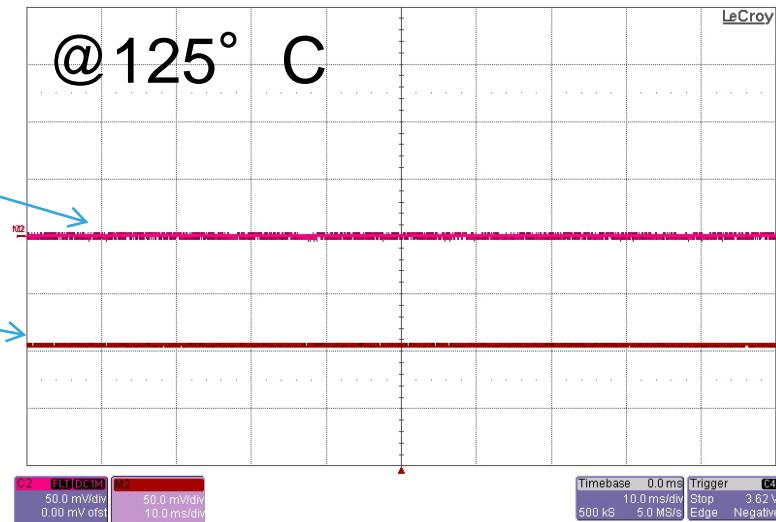
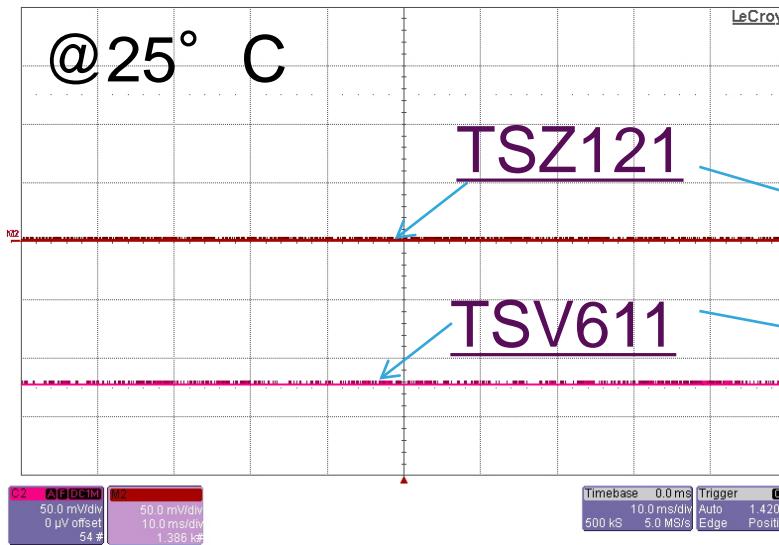
	Maximum V_{IO}	Maximum offset at ADC	Equivalent effective ADC
<u>TSZ121</u>	$5 \text{ }\mu\text{V}$	$55 \text{ }\mu\text{V}$	~12 bits
<u>TS507</u>	$100 \text{ }\mu\text{V}$	1.1 mV	~11 bits
<u>TS512A</u>	$500 \text{ }\mu\text{V}$	5.5 mV	~9 bits
<u>TS512</u>	2.5 mV	27.5 mV	~7 bits

$\Delta V_{io}/\Delta T$ and Calibration



$$V_{out} = V_{in} \left(\frac{-10k\Omega}{100\Omega} \right) \pm V_{io} \left(1 + \frac{10k\Omega}{100\Omega} \right) \quad (1)$$

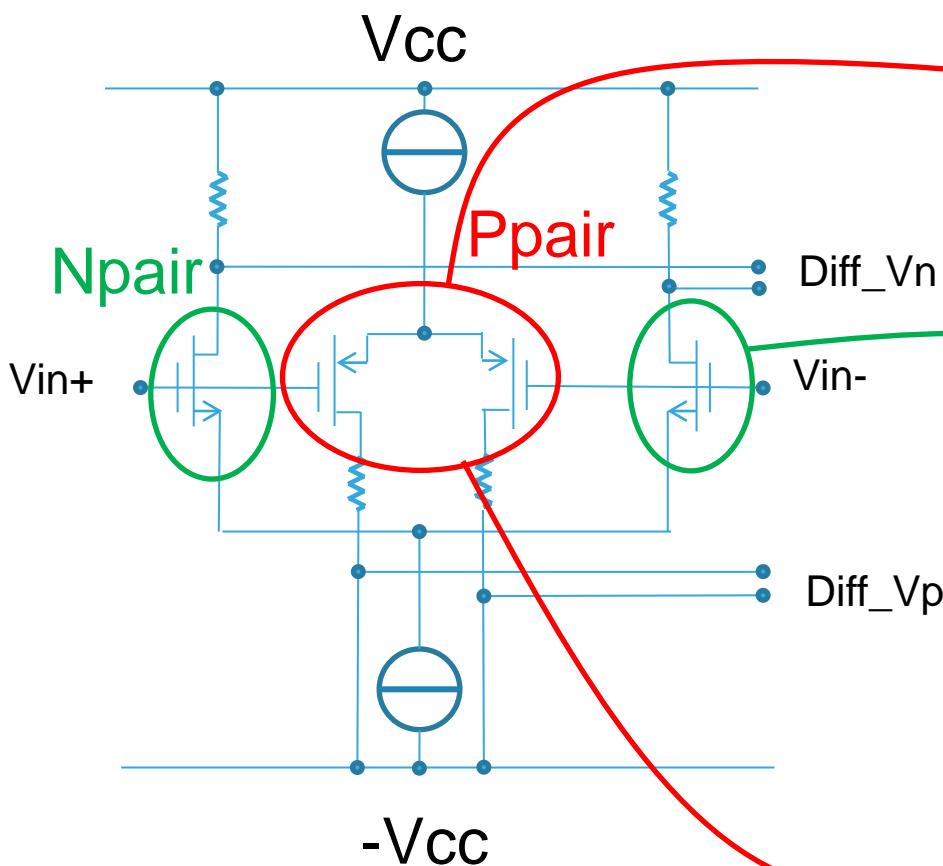
$$V_{out} = V_{in} \left(\frac{-10k\Omega}{100\Omega} \right) \pm (V_{io} \pm dT \left(\frac{\Delta V_{io}}{\Delta T} \right)) \left(1 + \frac{10k\Omega}{100\Omega} \right) \quad (2)$$



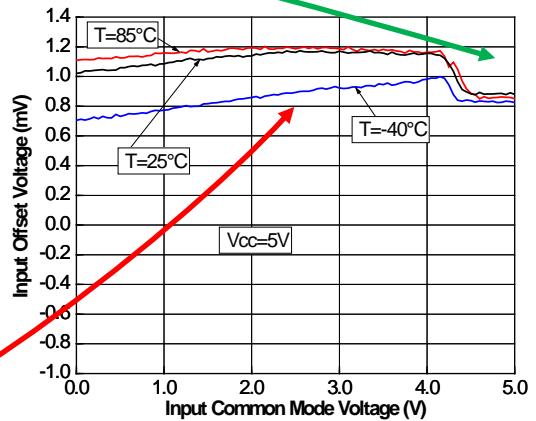
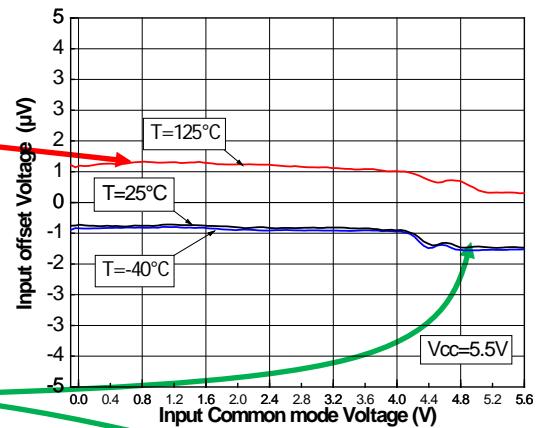
	$V_{io} @25^\circ\text{C} \text{ max}$	$\Delta V_{io}/\Delta T \text{ max}$
TSZ121	5μV	30nV/°C
TSV611	4mV	10μV/°C

Common mode rejection ratio

Input stage of a CMOS op amp



TSZ121



TSV611



Impact of CMRR on a battery monitoring High-side current sensing

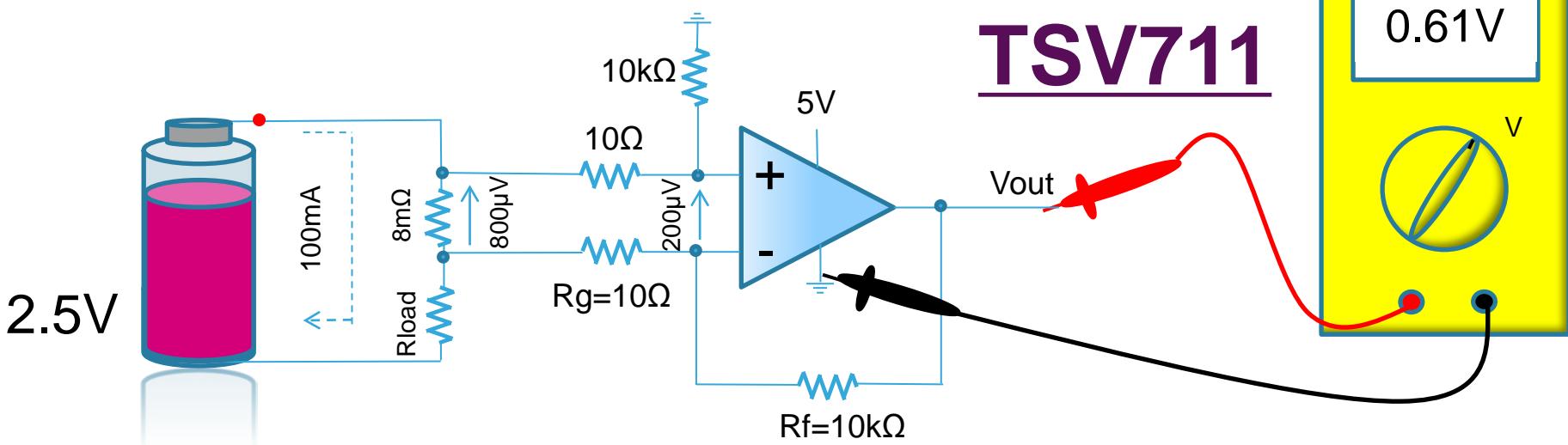
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$$\text{CMRR}_{\text{res}} = \frac{1 + \frac{R_f}{R_g}}{4\epsilon}$$

$$V_{\text{out}} = 0.8 - \left(1 + \frac{R_f}{R_g}\right) \cdot V_{\text{io}} \pm \frac{v_{\text{bat}}}{\text{CMRR}_{\text{res}}} \left(\frac{R_f}{R_g}\right) \pm \frac{v_{\text{icm}} - v_{\text{cc}}/2}{\text{CMRR}_{\text{op}}} \left(1 + \frac{R_f}{R_g}\right)$$

With $\epsilon=0.1\%$ precision resistance
and a gain of 1000

The CMRR of the whole schematics is 250250 (108 dB)



TSV711	Impact on V_{out}	Error %
V_{io}	0.2V	25%
CMRR _{res} @ 4.2V (108dB)	16.8mV	2.1%
CMRR _{op} @ 4.2V (74dB)	340mV	42.5%
CMRR _{res} @ 2.5V (108dB)	10mV	1.2%
CMRR _{op} @ 2.5V (74dB)	0mV	0%

Impact of CMRR on a battery monitoring High-side current sensing

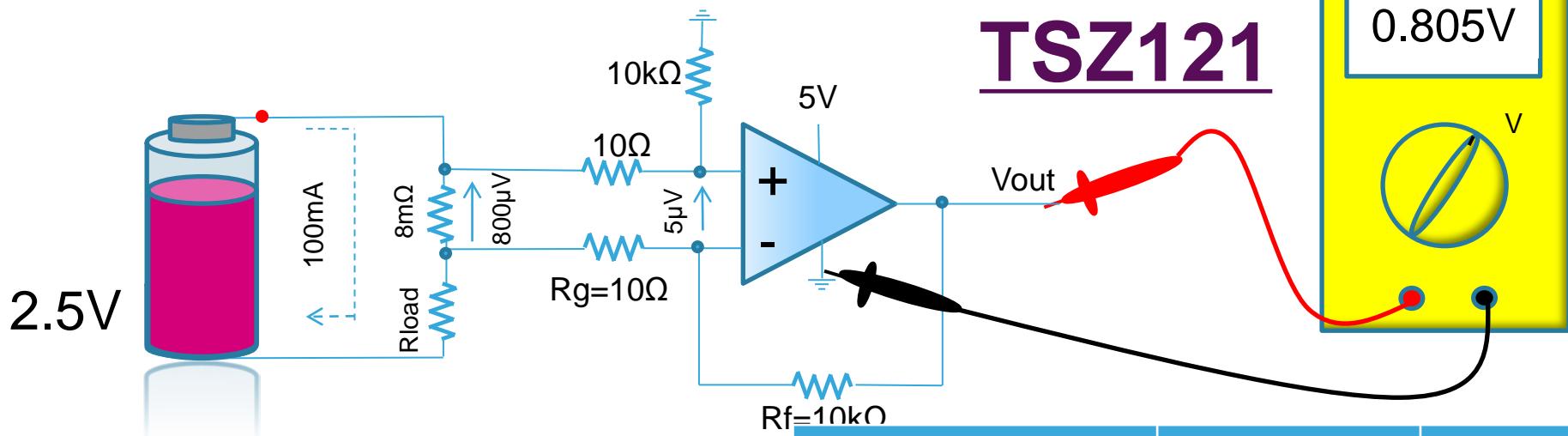
11

$$\text{CMRR}_{\text{res}} = \frac{1 + \frac{R_f}{R_g}}{4\epsilon}$$

$$V_{\text{out}} = 0.8 - \left(1 + \frac{R_f}{R_g}\right) \cdot V_{\text{io}} \pm \frac{v_{\text{bat}}}{\text{CMRR}_{\text{res}}} \left(\frac{R_f}{R_g}\right) \pm \frac{v_{\text{icm}} - v_{\text{cc}}/2}{\text{CMRR}_{\text{op}}} \left(1 + \frac{R_f}{R_g}\right)$$

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<u>TSV711</u>	Impact on Vout	Error %
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CMRR _{res} @ 2.5V (108dB)	10mV	1.2%
CMRR _{op} @ 2.5V (74dB)	0mV	0%

<u>TSZ121</u>	Impact on Vout	Error %
V _{io}	0.005V	0.5%
CMRR _{res} @ 4.2V (108dB)	16.8mV	2.1%
CMRR _{op} @ 4.2V (115dB)	3mV	0.4%
CMRR _{res} @ 2.5V (108dB)	10mV	1.2%
CMRR _{op} @ 2.5V (115dB)	0mV	0%



V_{IO} , CMRR, PSRR and A_{VD}

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$$V_{id} = V_{io} + \frac{\partial V_{id}}{\partial V_{out}} \Delta V_{out} + \frac{\partial V_{id}}{\partial V_{icm}} \Delta V_{icm} + \frac{\partial V_{id}}{\partial V_{cc}} \Delta V_{cc} + \frac{\partial V_{id}}{\partial T} \Delta T(1)$$

Diagram illustrating the components of V_{id} :

- Input Offset** (blue arrow): V_{io}
- AVD** (blue arrow): $\frac{\partial V_{id}}{\partial V_{out}} \Delta V_{out}$
- CMRR** (blue arrow): $\frac{\partial V_{id}}{\partial V_{icm}} \Delta V_{icm}$
- PSRR** (blue arrow): $\frac{\partial V_{id}}{\partial V_{cc}} \Delta V_{cc}$
- Input Offset drift** (blue arrow): $\frac{\partial V_{id}}{\partial T} \Delta T(1)$

We define: $Avd = -20 \log \left(\left| \frac{\partial V_{id}}{\partial V_{out}} \right| \right)$, $CMRR = -20 \log \left(\left| \frac{\partial V_{id}}{\partial V_{icm}} \right| \right)$, $SVR = -20 \log \left(\left| \frac{\partial V_{id}}{\partial V_{cc}} \right| \right)$ and $DV_{io} = \left| \frac{\partial V_{id}}{\partial T} \right|$

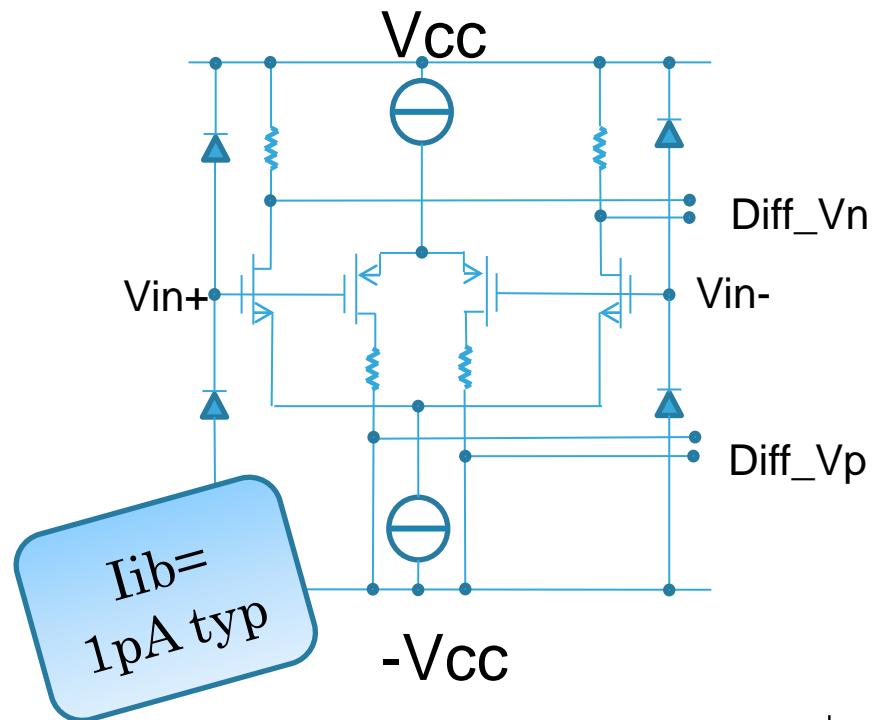


Input bias current

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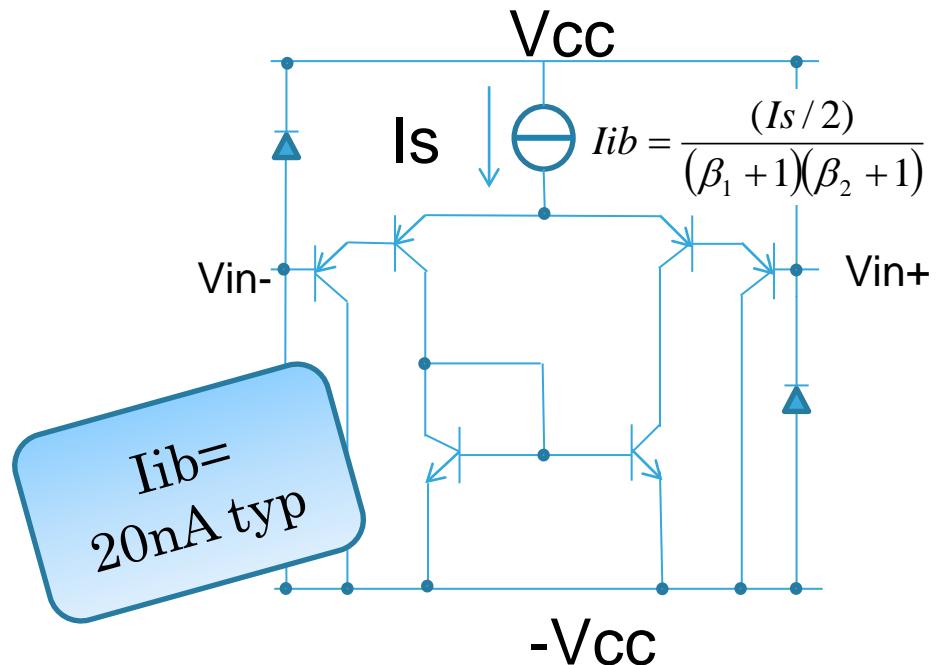
CMOS

- No gate current only diode leakage



BIPOLAR

- Current in/out (NPN/PNP) in the base



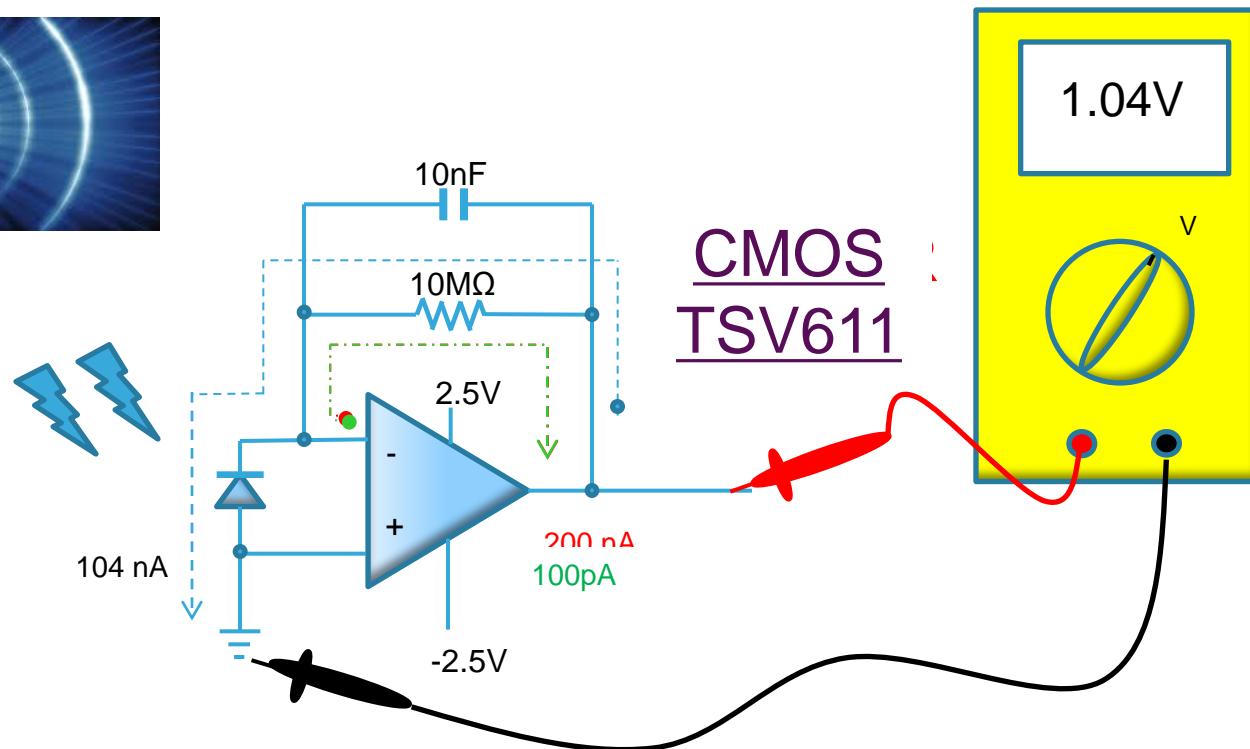
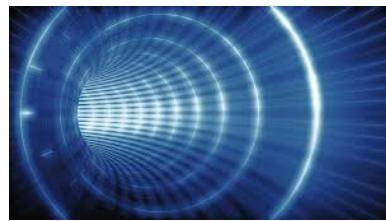
$$I_{ib} = \left| \frac{I_{ibn} + I_{ibp}}{2} \right|$$



UV sensor application

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UV source Index 4



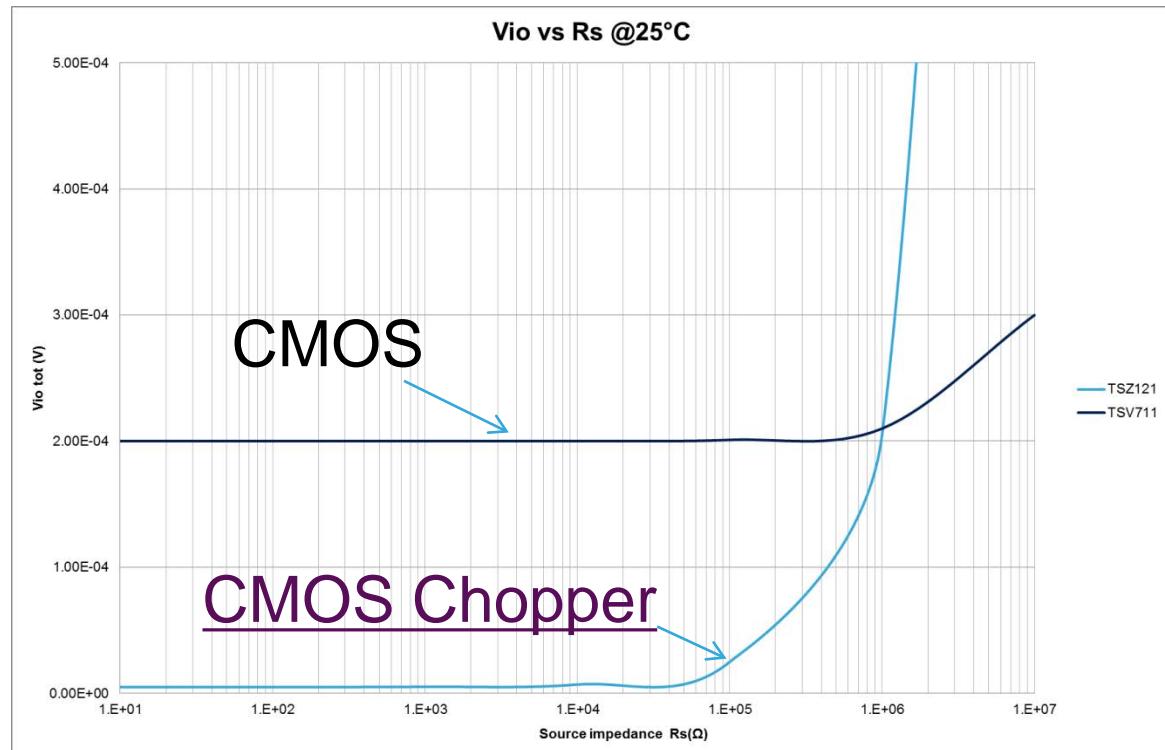
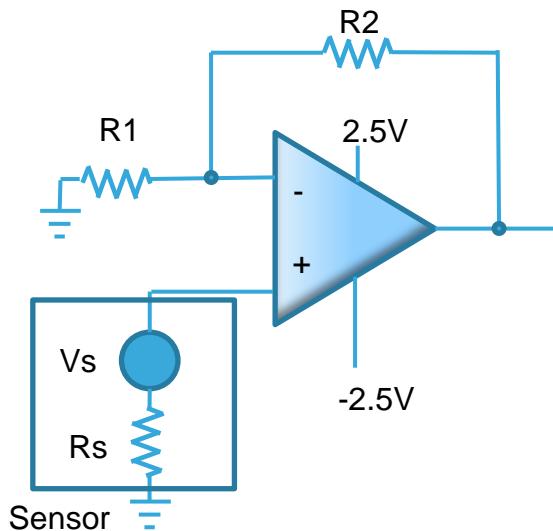
CMOS
TSV611

UV table translation for the UV sensor and Gain of 10M						
UV1	UV2	UV3	UV4	UV5	UV6	UV7
0.26 V	0.52 V	0.78 V	1.04 V	1.3 V	1.56 V	1.82 V



Is the TSZ121 chopper always a good choice?

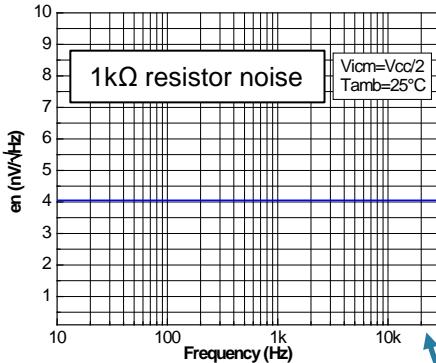
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$$V_{io\ tot} = V_{io} + R_s \cdot I_n \quad (1)$$

$$R_s > \frac{V_{io}}{I_n} \quad (2)$$

Noise sources of an op amp



Resistors generate a white noise with a spectral density of:

$$e_n = \sqrt{4kTR} \quad V\sqrt{Hz}^{-\frac{1}{2}}$$

Where

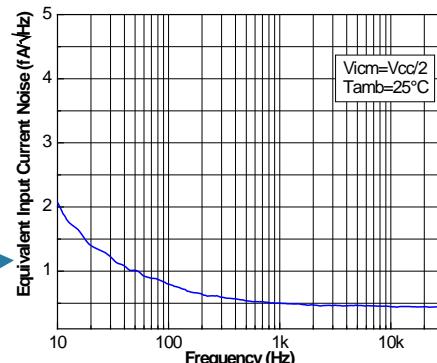
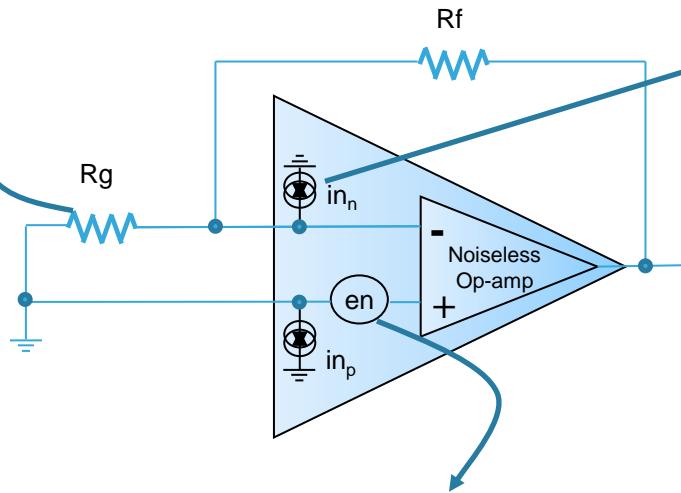
$$k = 1.38 \cdot 10^{-23} \quad JK^{-1}$$

(Boltzmann's constant)

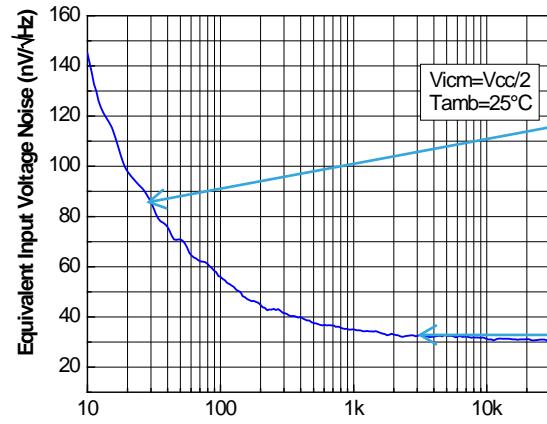
$$T = T(\text{°C}) + 273.15$$

(Temperature in Kelvin)

There are 5 sources of noise



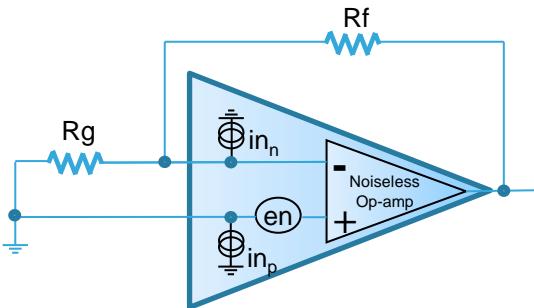
For CMOS input op amps
Input noise current is extremely low (0.5fA/√Hz) and generally does not affect design



$$\frac{1}{f} \text{ noise (flicker noise)} \\ \mathbf{enf(f) = \sqrt{\frac{enf(1Hz)}{f}} V/\sqrt{Hz}}$$

White noise
 $en \text{ V}/\sqrt{\text{Hz}}$

Contribution of each source of noise



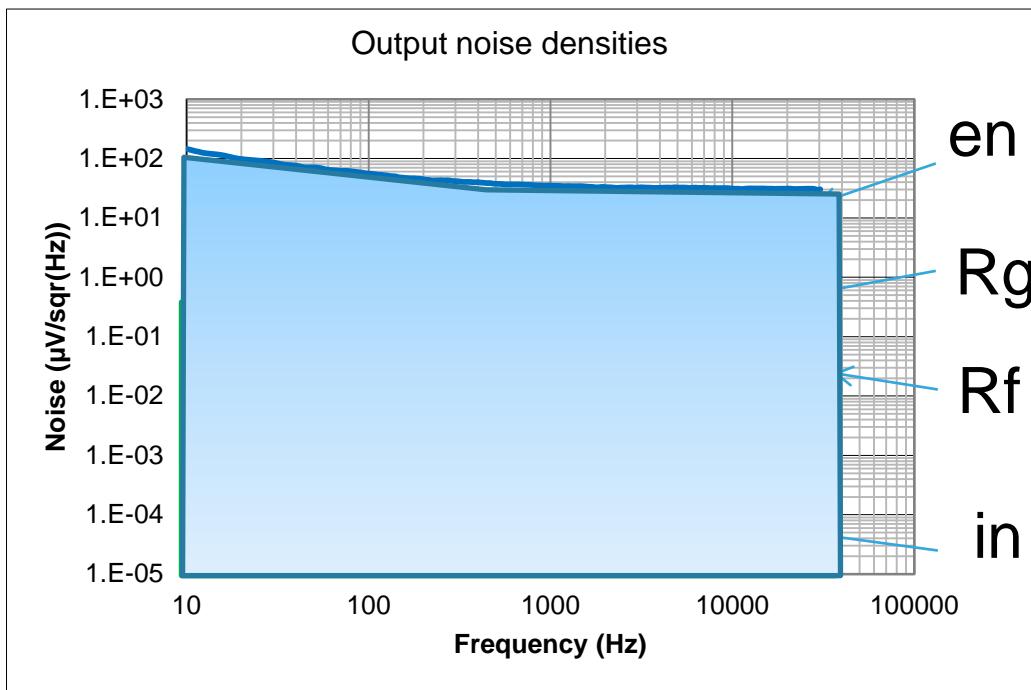
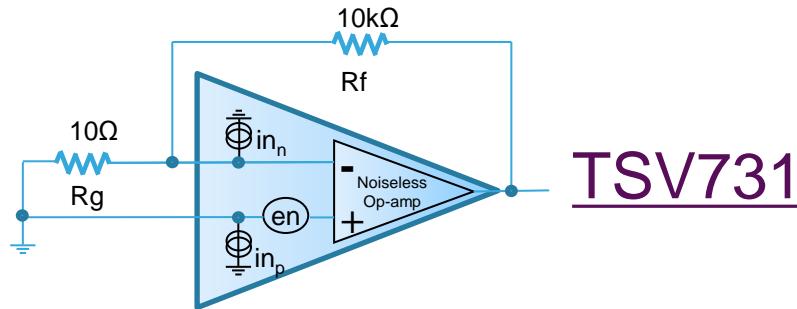
$$V_{out\ rms} = \sqrt{\int_{fL}^{fH} \left[e_n^2 \left(1 + \frac{R_f}{R_g} \right)^2 + R_f^2 I_{nn}^2 + 4kTR_g \left(\frac{R_f}{R_g} \right)^2 + 4kTR_f \right] df}$$

Noise source	Spectral density noise referred to the output	RMS noise value over a given bandwidth referred to the output
e_n	$en \cdot \left(1 + \frac{R_f}{R_g} \right)$	$(1 + \frac{R_f}{R_g}) \cdot \sqrt{en^2(FH - FL)} \text{ if white noise}$ $(1 + \frac{R_f}{R_g}) \cdot \sqrt{en^2(1\text{Hz}) \cdot \ln(\frac{FH}{FL})} \text{ if 1/f noise}$
I_{nn}	$Inn \cdot R_f$	$R_f \cdot \sqrt{Inn^2(FH - FL)}$ if white noise
R_g	$\frac{R_f}{R_g} \cdot \sqrt{4 \cdot k \cdot T \cdot Rg}$	$\frac{R_f}{R_g} \cdot \sqrt{4 \cdot k \cdot T \cdot Rg \cdot (FH - FL)}$
R_f	$\sqrt{4 \cdot k \cdot T \cdot Rf}$	$\sqrt{4 \cdot k \cdot T \cdot Rf \cdot (FH - FL)}$



Contribution of each source of noise

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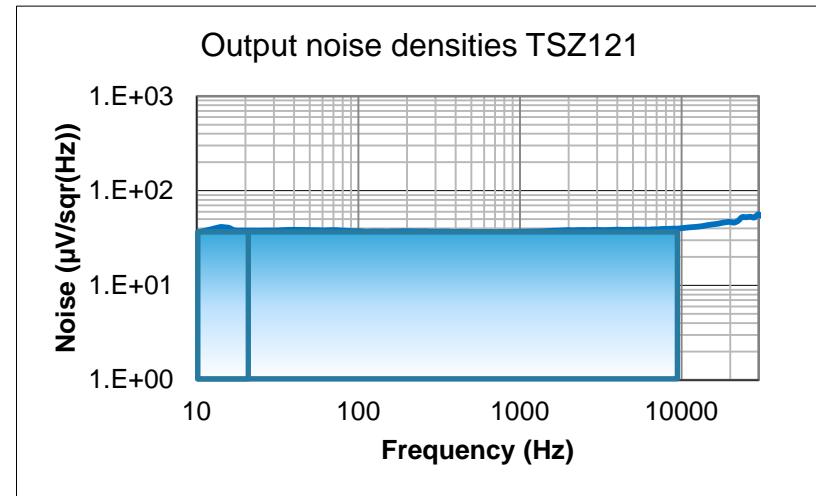
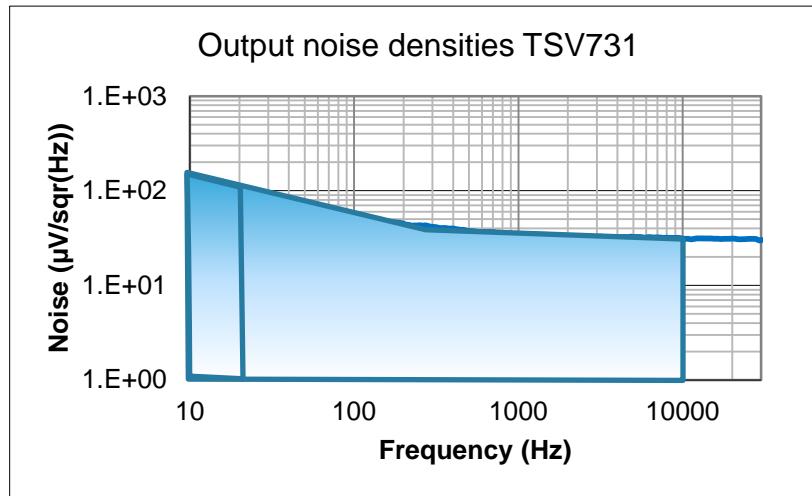
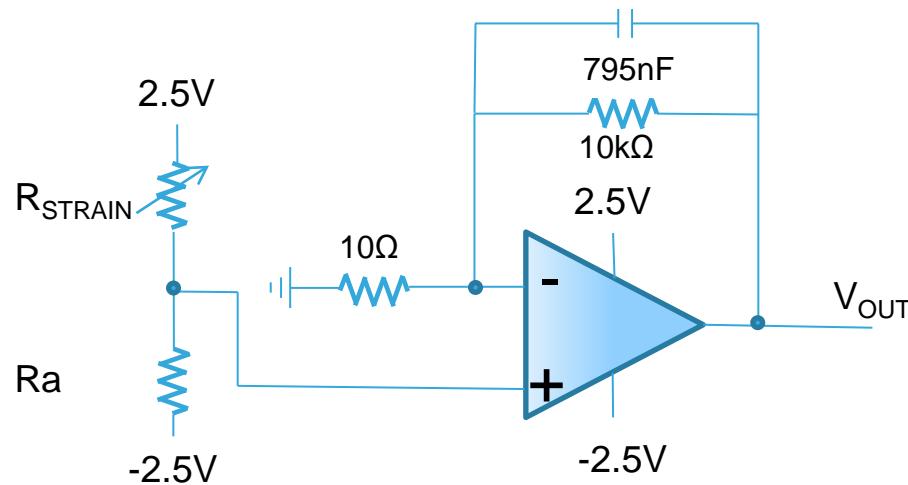
Noise voltage contribution to the output BW=30kHz

Noise Source	en Vrms
OPAMP	en $5.37 \cdot 10^{-3}$
	In $8.66 \cdot 10^{-9}$
THERMAL	Rf $2.2 \cdot 10^{-6}$
	Rg $70.5 \cdot 10^{-6}$



Impact of noise in a application

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Bandwidth 20Hz



en_Vout_{Rms}=0.69mV_{Rms}

en_Vout_{Rms}=0.16mV_{Rms}



Summary of the errors impacting precision

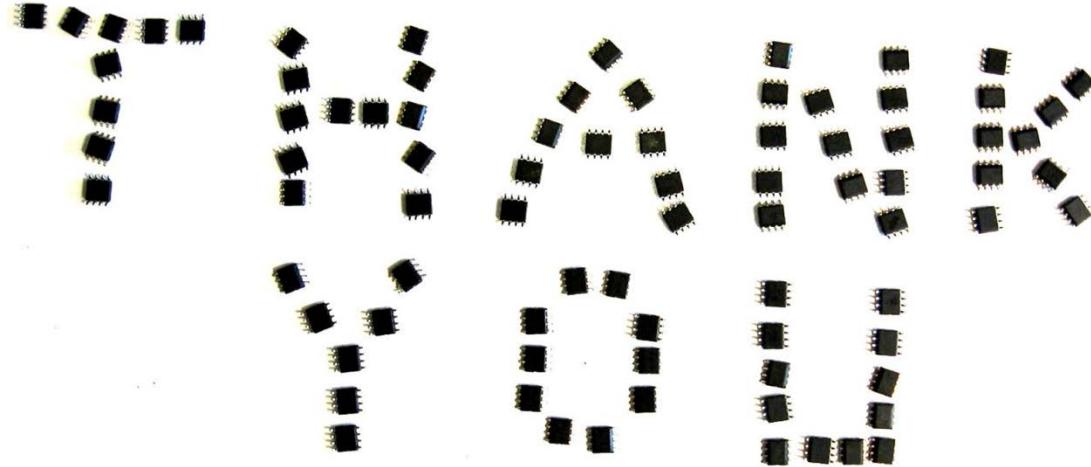
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Input Referred Error:

The various non-ideal components of an operational amplifier all contribute to its total input referred error.

	Parameter value	Condition	Real Value
Offset	100 μ V	-	100 μ V
Offset drift	10 μ V/ $^{\circ}$ C	70 $^{\circ}$ C	700 μ V
CMRR	80dB	0-3V	300 μ V
PSRR	80dB	5V +/- 10%	50 μ V
Noise	10 μ Vpp	0.1-10Hz	10 μ Vpp

All the errors are summed and must be compared to the input signal.



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